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(71) Applicant (for all designated States except US): SEMI-
CONDUCTOR ENERGY LABORATORY CO., LTD.
[JP/JP]; 398, Hase, Atsugi-shi, Kanagawa, 2430036 (JP).

(72) Inventors; and

(75) Inventors/Applicants (for US only): ARAI, Yasuyuki
[JP/JP]; c/o SEMICONDUCTOR ENERGY LABORA-
TORY CO., LTD., 398, Hase, Atsugi-shi, Kanagawa,

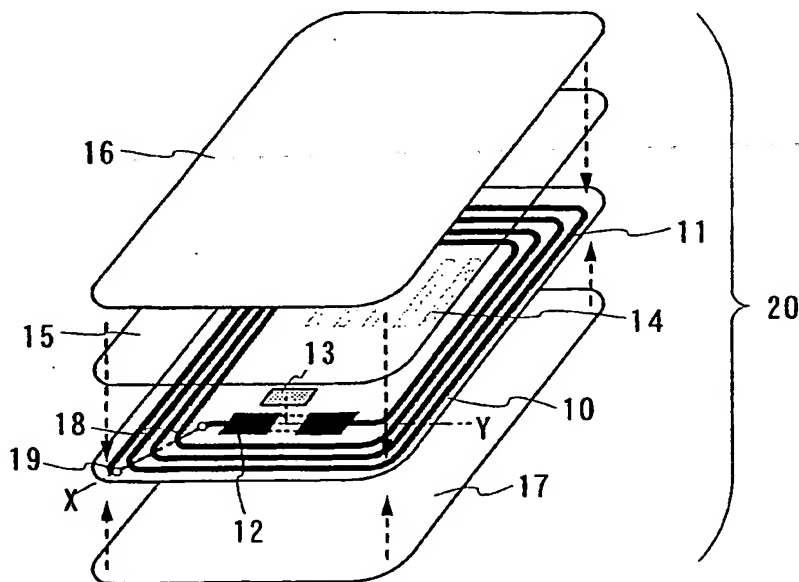
2430036 (JP). AKIBA, Mai [JP/JP]; c/o SEMICON-
DUCTOR ENERGY LABORATORY CO., LTD., 398, Hase,
Atsugi-shi, Kanagawa, 2430036 (JP). TACHIMURA,
Yuko [JP/JP]; c/o SEMICONDUCTOR ENERGY LAB-
ORATORY CO., LTD., 398, Hase, Atsugi-shi, Kanagawa,
2430036 (JP). KANNO, Yohei [JP/JP]; c/o SEMICON-
DUCTOR ENERGY LABORATORY CO., LTD., 398,
Hase, Atsugi-shi, Kanagawa, 2430036 (JP).

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(54) Title: ID LABEL, ID CARD, AND ID TAG



(57) Abstract: As a non-contact ID label, ID tag and the like being widespread, it is required to manufacture a considerable quantity of ID labels at quite a low cost. An ID label attached to a product is, for example, required to be manufactured at 1 to several yens each, or preferably less than one yen. Thus, such a structure and a process are demanded that an ID label can be manufactured in a large quantity at a low cost. A thin film integrated circuit device included in the ID label, the ID card, and the ID tag of the invention each includes a thin film active element such as a thin film transistor (TFT). Therefore, by peeling a substrate on which TFTs are formed for separating elements, the ID label and the like can be manufactured in a large quantity at a low cost.

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